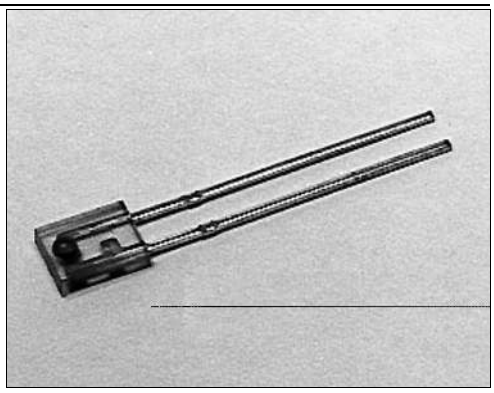
SDP8406

Silicon Phototransistor

FEATURES

- Side-looking plastic package
- 50° (nominal) acceptance angle
- Wide sensitivity ranges
- Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes



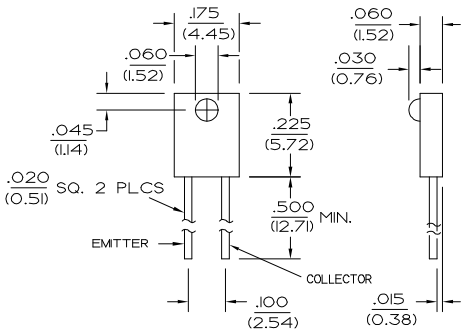
INFRA-21.TIF

DESCRIPTION

The SDP8406 is an NPN silicon phototransistor molded in a side-looking clear plastic package. The chip is positioned to accept radiation through a plastic lens from the side of the package.

OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals	±0.005(0.12)
	2 plc decimals	±0.020(0.51)



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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current	I_L				mA	V_{CE}=5 V
SDP8406-001		0.15		1.90		H=1 mW/cm² (1)
SDP8406-002		1.80		3.60		
SDP8406-003		3.40		6.50		
SDP8406-004		6.40		12.0		
Collector Dark Current	I_{CEO}			100	nA	V_{CE}=15 V, H=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	I_C=100 µA
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5.0			V	I_E=100 µA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$			0.4	V	I_C=I_L/8 H=1 mW/cm²
Angular Response (2)	Ø		50		degr.	I_F=Constant
Rise And Fall Time	t_r, t_f		15		µs	V_{CC}=5 V, I_L=1 mA R_L=1000 Ω

Notes
1. The radiation source is an IRED with a peak wavelength of 935 nm.
2. Angular response is defined as the total included angle between the half sensitivity points.

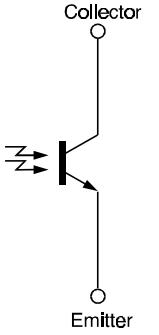
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW (1)
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C

Notes
1. Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.

SCHEMATIC



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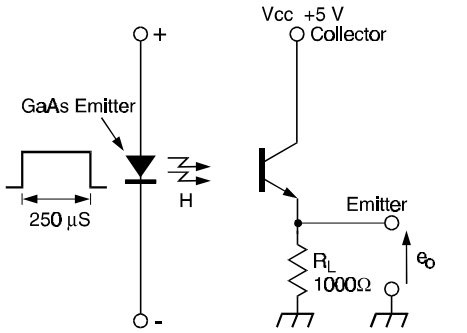
SWITCHING TIME TEST CIRCUIT

cir_015.cdr



SWITCHING WAVEFORM

cir_004.cdr

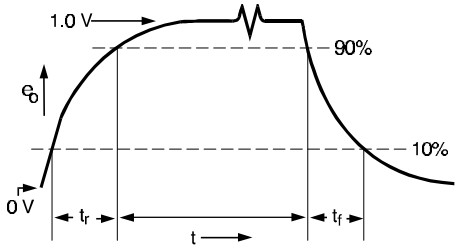


Fig. 1 Responsivity vs Angular Displacement

gra_054.ds4

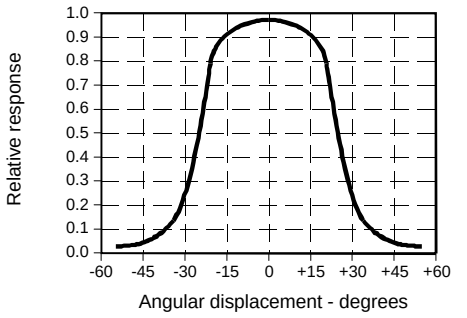


Fig. 2 Collector Current vs Ambient Temperature

gra_039.ds4

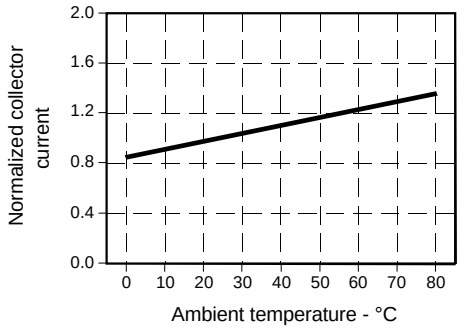


Fig. 3 Dark Current vs Temperature

gra_301.cdr

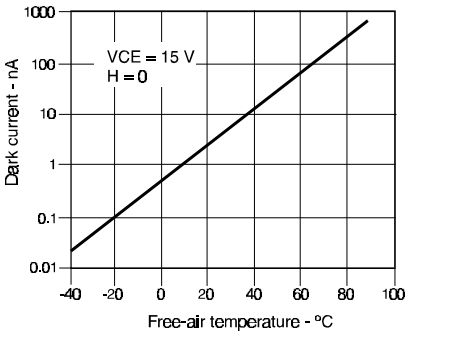


Fig. 4 Non-Saturated Switching Time vs Load Resistance

gra_041.ds4

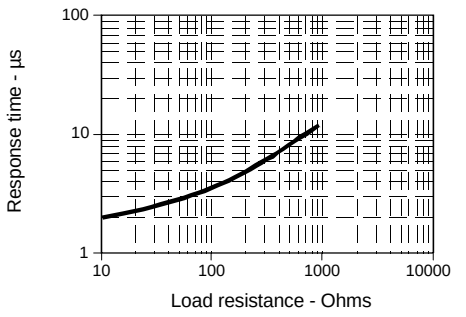


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Fig. 5 Spectral Responsivity

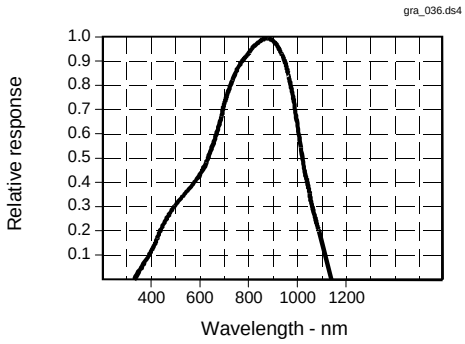
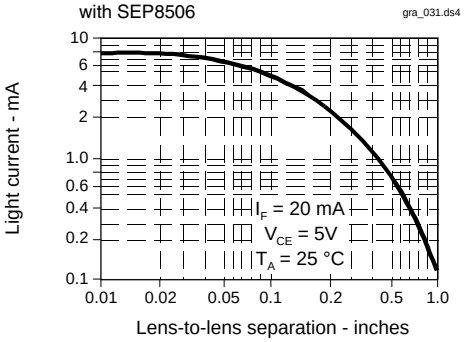


Fig. 6 Coupling Characteristics with SEP8506



All Performance Curves Show Typical Values